



# IESL SEMINAR

**Wednesday 15/03/2023, 12:00**  
**FORTH Seminar Room 1**

## **Control of the Exciton and Spin/Valley Properties in Atomically Thin Transition Metal Dichalcogenides**

**Dr. Xavier Marie**

Université de Toulouse, INSA-CNRS-UPS, Toulouse, France  
e-mail: [marie@insa-toulouse.fr](mailto:marie@insa-toulouse.fr)

### Abstract

In this talk I will first recall briefly the general properties of 2D excitons in Transition Metal Dichalcogenides (TMD) monolayers: giant binding energy, oscillator strength, exchange interactions, spin/valley locking ...<sup>1</sup>.

Encapsulation of TMD monolayers in hexagonal boron nitride (hBN) yields narrow optical transitions approaching the homogeneous exciton linewidth<sup>2,3</sup>. We have demonstrated that the exciton radiative rate in these van der Waals heterostructures can be tailored by a simple change of the hBN encapsulation layer thickness as a consequence of the Purcell effect<sup>4</sup>.

We also measured the exciton fine structure by magneto-photoluminescence spectroscopy in magnetic fields up to 30 T<sup>5,6</sup>. I will show that the bright-dark exciton splitting can be tuned by a few meV, as a result of a significant Lamb shift of the optically active exciton which arises from emission and absorption of virtual photons triggered by the vacuum fluctuations of the electromagnetic field<sup>7</sup>.

Finally I will present recent experimental results on spin/valley pumping of resident electrons in WSe<sub>2</sub> and WS<sub>2</sub> monolayers<sup>8</sup>. Using a spatially-resolved optical pump-probe experiment, we measure the lateral transport of spin/valley polarized electrons over very long distances (tens of micrometers)<sup>9</sup>. These results highlight the key role played by the spin-valley locking effect in TMD monolayers on the pumping efficiency and the polarized electron transport.

<sup>1</sup> G. Wang *et al*, Rev. Mod. Phys. **90**, 021001 (2018)

<sup>2</sup> F. Cadiz *et al*, Phys. Rev. X **7**, 021026 (2017)

<sup>3</sup> G. Wang *et al*, Phys. Rev. Lett. **119**, 047401 (2017)

<sup>4</sup> H. Fang *et al*, Phys. Rev. Lett. **123**, 067401 (2019)

<sup>5</sup> C. Robert *et al*, Phys. Rev. Lett. **126**, 067403 (2021)

<sup>6</sup> C. Robert *et al*, Nature Com. **11**, 4037 (2020)

<sup>7</sup> L. Ren *et al*, submitted (2023)

<sup>8</sup> C. Robert *et al*, Nature Com. **12**, 5455 (2021)

<sup>9</sup> C. Robert *et al*, Phys. Rev. Lett. **129**, 027402 (2022)

